

Title (en)

DAMASCENE STRUCTURE AND METHOD FOR FORMING A DAMASCENE STRUCTURE

Title (de)

DAMASZENSTRUKTUR UND VERFAHREN ZUR HERSTELLUNG EINER DAMASZENSTRUKTUR

Title (fr)

STRUCTURE DAMASQUINEE ET PROCEDE DE FORMATION D'UNE STRUCTURE DAMASQUINEE

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Application

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Abstract (en)

[origin: WO0154191A1] A damascene structure having a reduced overall dielectric constant and a method for forming such a structure is disclosed. In one embodiment, the present embodiment deposits a blanket coating (206, 306) of etch stop layer material over an underlying structure. In the present embodiment, the underlying structure includes a first region (202, 302) to which an interconnect will be subsequently be formed. Next, the present embodiment selectively removes portions of the blanket coating of the etch stop layer material. More specifically, in the present embodiment, the etch stop layer material is removed from above a second region (208, 304) of the underlying structure. In the present embodiment, the second region of the underlying structure will not subsequently have the interconnect formed thereto. In so doing, the present embodiment eliminates the presence of superfluous etch stop layer material. As a result, the overall dielectric constant of the intermetal filmstack is reduced as compared to conventional damascene structures.

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